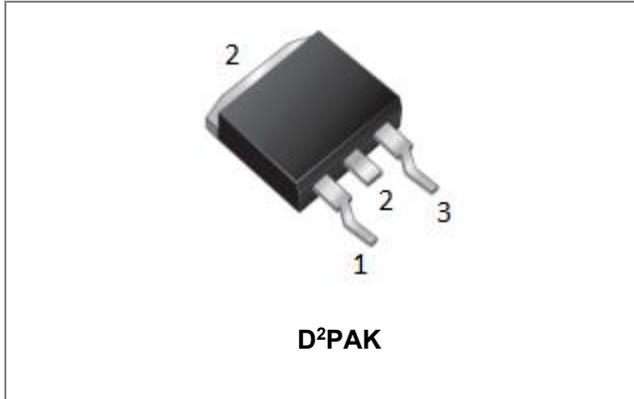


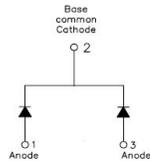
MBRB40200CT SCHOTTKY RECTIFIER



Features

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: 100% Pure Tin
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings (limiting values, at 25 °C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	200	V
Average Rectified Forward Current	I _{F(AV)}	T _c =128°C, In DC	20(Per Leg) 40(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse	396	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop (Per Leg) *	V _{F1}	@ 20A, Pulse, T _J = 25 °C	0.88	0.90	V
	V _{F2}	@ 20A, Pulse, T _J = 125 °C	0.70	0.80	V
Reverse Current (Per Leg) *	I _{R1}	@V _R = rated V _R , T _J = 25 °C	0.0001	1.0	mA
	I _{R2}	@V _R = rated V _R , T _J = 125 °C	0.1	11.0	mA
Junction Capacitance(Per Leg)	C _T	@V _R = 5V, T _C = 25 °C, f _{SIG} = 1MHz	300	450	pF
Series Inductance(Per Leg)	L _S	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

* Pulse width < 300 μs, duty cycle < 2%

- China - Germany - Korea - Singapore - United States •
- <http://www.smc-diodes.com> - sales@smc-diodes.com •

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-	-55 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Case(Per Leg)	$R_{\theta\text{JC}}$	DC operation	1.2	$^{\circ}\text{C}/\text{W}$
Approximate Weight	wt	-	1.85	g
Case Style	D ² PAK			

Ratings and Characteristics Curves

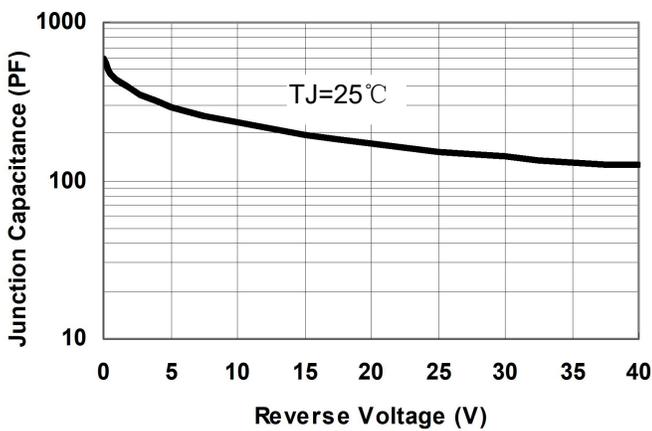


Fig.1-Typical Junction Capacitance

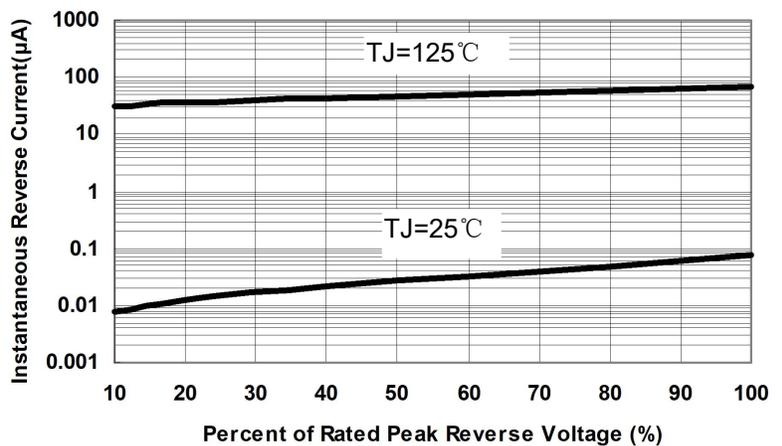


Fig.2-Typical Reverse Characteristics

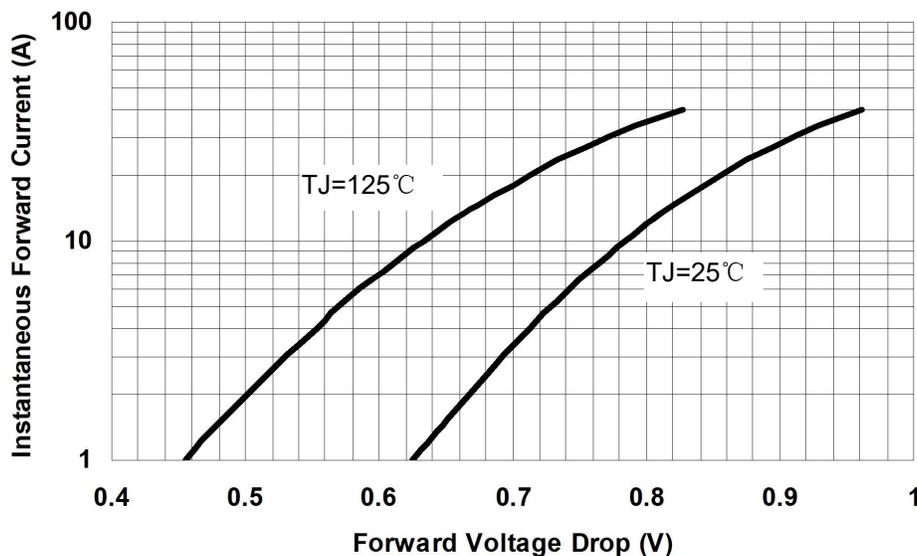
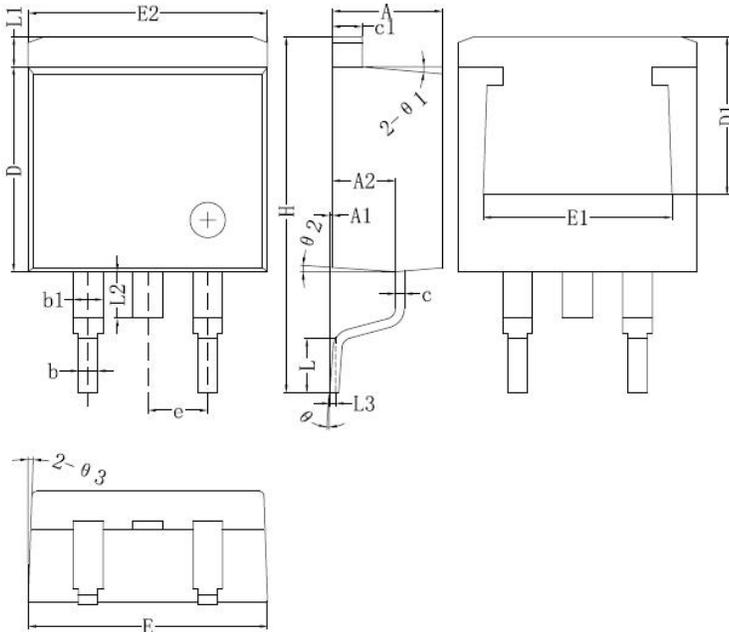


Fig.3-Typical Instantaneous Forward Voltage Characteristics

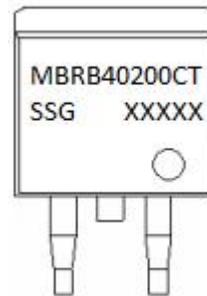
Mechanical Dimensions D²PAK


Symbol	Dimensions in millimeters	
	Min.	Max.
A	4.06	4.83
A1	0	0.26
b	0.51	0.99
b1	1.14	1.78
c	0.31	0.74
c1	1.14	1.65
D	8.38	9.65
D1	6.4	
E1	6.22	
E2	9.65	10.67
e	2.54BSC	
H	14.6	15.88
L	1.78	2.8
L1	-	1.68
L2	-	2.2
L3	0.255BSC	
Ø	0	8°

Ordering Information

Device	Package	Shipping
MBRB40200CT	D ² PAK	800pcs / reel
MBRB40200CTTR	D ² PAK	800pcs / reel

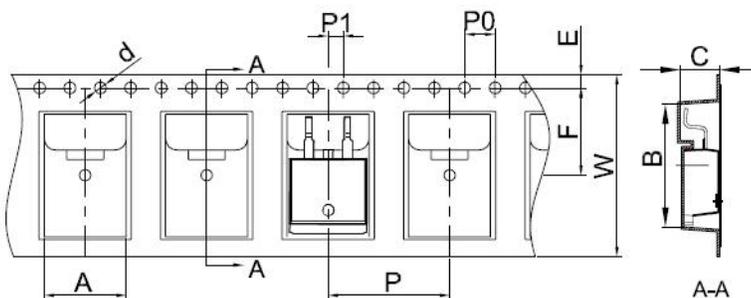
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram


Where XXXXX is YYWWL

MBR = Device Type
 B = Package type
 40 = Forward Current (40A)
 200 = Reverse Voltage(200V)
 CT = Configuration
 SSG = SSG
 YY = Year
 WW = Week
 L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Carrier Tape Specification D²PAK


SYMBOL	Millimeters	
	Min.	Max.
A	10.70	10.90
B	16.03	16.23
C	5.11	5.31
d	1.45	1.65
E	1.65	1.85
F	11.40	11.60
P0	3.90	4.10
P	15.90	16.10
P1	1.90	2.10
W	23.90	24.30

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